

HiPerFRED

$$V_{RRM} = 600V$$

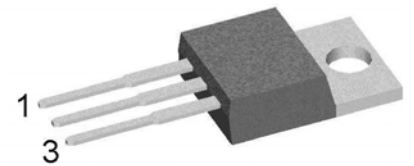
$$I_{FAV} = 2x \quad 10A$$

$$t_{rr} = 30ns$$

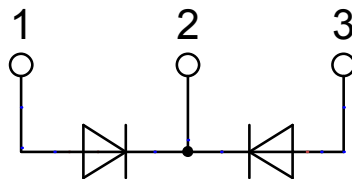
High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Common Cathode

Part number

DSEC16-06A



Backside: cathode

**Features / Advantages:**

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-220

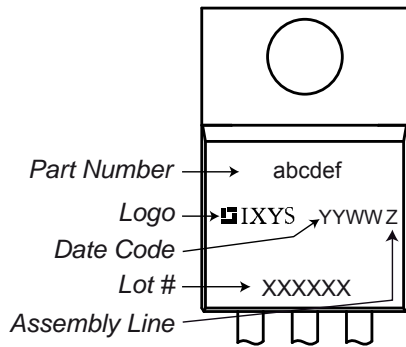
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					600	V
V_{RRM}	max. repetitive reverse blocking voltage					600	V
I_R	reverse current, drain current	$V_R = 600\text{ V}$	$T_{VJ} = 25^\circ\text{C}$			60	μA
		$V_R = 600\text{ V}$	$T_{VJ} = 150^\circ\text{C}$			0.25	mA
V_F	forward voltage drop	$I_F = 10\text{ A}$	$T_{VJ} = 25^\circ\text{C}$			2.10	V
						2.32	V
		$I_F = 10\text{ A}$	$T_{VJ} = 150^\circ\text{C}$			1.42	V
						1.68	V
I_{FAV}	average forward current	$T_C = 135^\circ\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 175^\circ\text{C}$			10	A
V_{FO}	threshold voltage	} for power loss calculation only				1.03	V
r_F	slope resistance					25.1	m Ω
R_{thJC}	thermal resistance junction to case					2.5	K/W
R_{thCH}	thermal resistance case to heatsink				0.50		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		60	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$		$T_{VJ} = 45^\circ\text{C}$		50	A
C_J	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$		$T_{VJ} = 25^\circ\text{C}$		6	pF
I_{RM}	max. reverse recovery current	} $I_F = 10\text{ A}; V_R = 100\text{ V}$		$T_{VJ} = 25^\circ\text{C}$		4	A
				$T_{VJ} = 100^\circ\text{C}$		6	A
t_{rr}	reverse recovery time	} $-di_F/dt = 200\text{ A}/\mu\text{s}$		$T_{VJ} = 25^\circ\text{C}$		30	ns
				$T_{VJ} = 100^\circ\text{C}$		90	ns

Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾			35	A
T_{stg}	storage temperature		-55		150	°C
T_{vj}	virtual junction temperature		-55		175	°C
Weight				2		g
M_D	mounting torque		0.4		0.6	Nm
F_C	mounting force with clip		20		60	N

¹⁾ I_{RMS} is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a common cathode/anode configuration with a non-isolated backside, the current capability can be increased by connecting the backside.

Product Marking



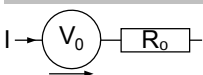
Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEC16-06A	DSEC16-06A	Tube	50	475130

Similar Part	Package	Voltage class
DSEC16-06AC	ISOPLUS220AB (3)	600

Equivalent Circuits for Simulation

* on die level

$T_{vj} = 175^\circ\text{C}$



Fast Diode

$V_{0\ max}$ threshold voltage

1.03

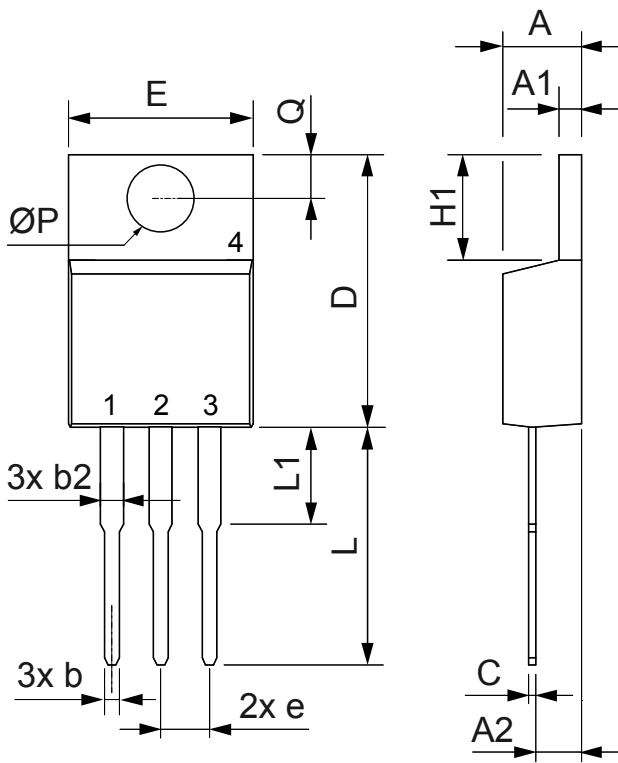
V

$R_{0\ max}$ slope resistance *

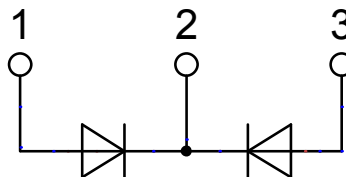
22

mΩ

Outlines TO-220



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	2.54	BSC	0.100	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
$\varnothing P$	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125



Fast Diode

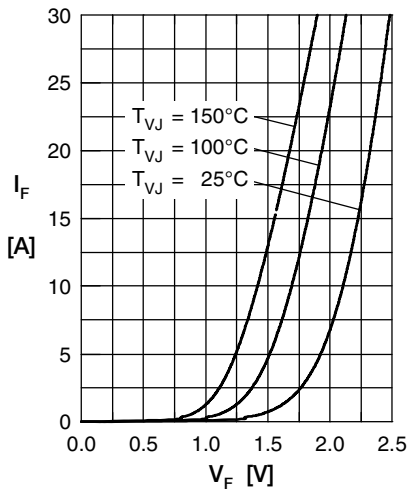


Fig. 1 Forward current I_F versus V_F

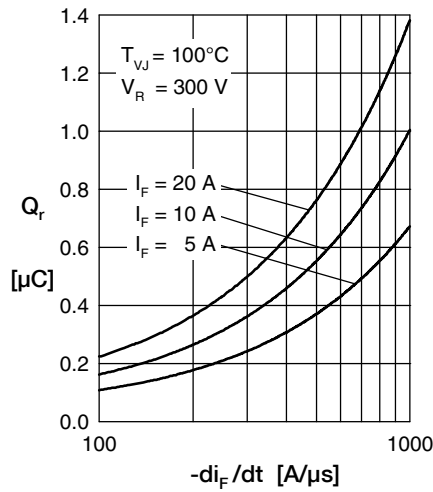


Fig. 2 Typ. reverse recov. charge Q_r versus $-di_F/dt$

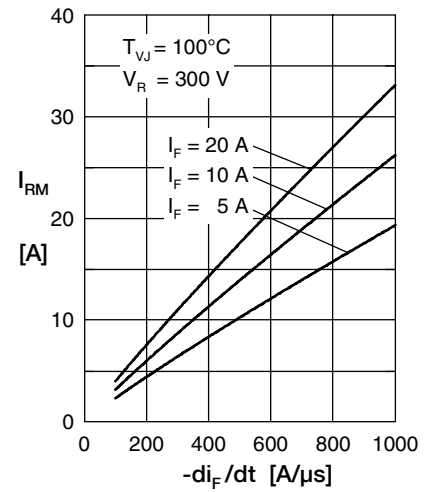


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

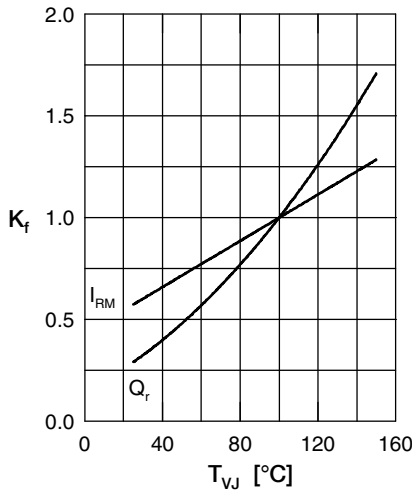


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

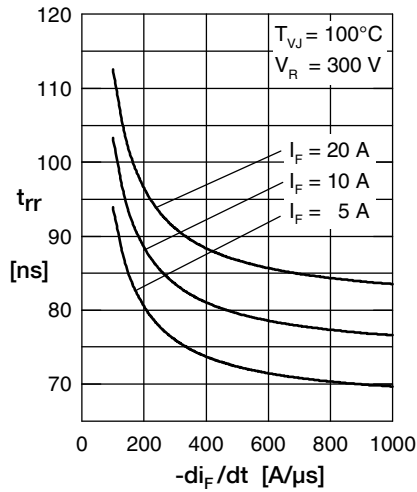


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

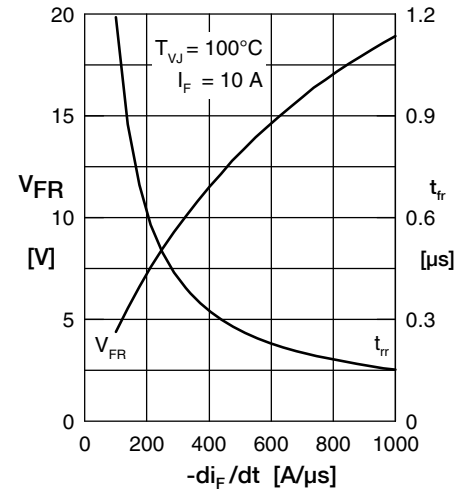


Fig. 6 Typ. peak forward voltage V_{FR} and t_{rr} versus di_F/dt

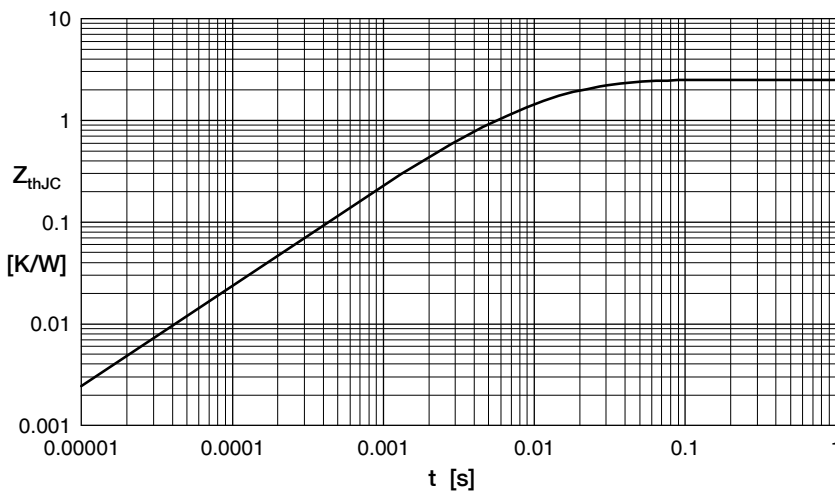


Fig. 7 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	1.449	0.0052
2	0.5578	0.0003
3	0.4931	0.0169